

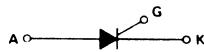
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**2N6167
thru
2N6170**

**SCRs
20 AMPERES RMS
100 thru 600 VOLTS**



Silicon Controlled Rectifier Reverse Blocking Triode Thyristor

... designed for industrial and consumer applications such as power supplies; battery chargers; temperature, motor, light and welder controls.

- Economical for a Wide Range of Uses
- High Surge Current — $I_{TSM} = 240$ Amps
- Rugged Construction in Isolated Stud Package

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
*Peak Repetitive Forward and Reverse Blocking Voltage (1) ($T_J = -40^\circ\text{C}$ to $+100^\circ\text{C}$) 2N6167 2N6168 2N6169 2N6170	V_{DRM} or V_{RRM}	100 200 400 600	Volts
*Non-Repetitive Peak Reverse Blocking Voltage ($t \leq 5$ ms) 2N6167 2N6168 2N6169 2N6170	V_{RSM}	150 250 450 650	Volts
*Average Forward Current ($T_C = -40$ to $+65^\circ\text{C}$) ($+85^\circ\text{C}$)	$I_{T(AV)}$	13 6.5	Amps
*Peak Surge Current (One cycle, 60 Hz) ($T_C = +65^\circ\text{C}$) (1.5 ms pulse @ $T_J = 100^\circ\text{C}$) Preceded and followed by no current or Voltage	I_{TSM}	240 560	Amps
Circuit Fusing ($T_J = -40$ to $+100^\circ\text{C}$) ($t = 1$ to 8.3 ms)	I_{2t}	235	A^2s
*Peak Gate Power	P_{GM}	5	Watts
*Average Gate Power	$P_{G(AV)}$	0.5	Watt

*Indicates JEDEC Registered Data.

(cont.)

(1) Ratings apply for zero or negative gate voltage. Devices shall not have a positive bias applied to the gate concurrently with a negative potential on the anode. Devices should not be tested with a constant current source for forward or reverse blocking capability such that the voltage applied exceeds the rated blocking voltage.

MAXIMUM RATINGS — continued

Rating	Symbol	Value	Unit
*Peak Forward Gate Current	I _{GFM}	2	Amps
*Operating Junction Temperature Range	T _J	-40 to +100	°C
*Storage Temperature Range	T _{stg}	-40 to +150	°C
*Stud Torque	—	30	in. lb.

***THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R _{θJC}	1.5	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
*Peak Forward or Reverse Blocking Current (Rated V _{DRM} or V _{RRM} , gate open, T _C = 100°C) 2N6167 2N6168 2N6169 2N6170	I _{DRM} , I _{RRM}	—	1	2	mA
(Rated V _{DRM} or V _{RRM} , gate open, T _C = 25°C) All Devices	—	—	1	2.5	μA
*Peak Forward "On" Voltage (I _{TM} = 41 A Peak)	V _{TM}	—	1.5	1.7	Volts
Gate Trigger Current, Continuous dc (V _D = 12 V, R _L = 24 Ω)	I _{GT}	—	—	75	mA
Gate Trigger Voltage, Continuous dc (V _D = 12 V, R _L = 24 Ω)	V _{GT}	—	0.8 0.63	2.5 1.6	Volts
Holding Current (V _D = 12 V, gate open, I _T = 200 mA)	I _H	—	— 3.5	90 50	mA
*Turn-On Time (t _d + t _r) (I _{TM} = 41 Adc, V _D = Rated V _{DRM} , I _{GT} = 200 mAadc, Rise Time ≤ 0.05 μs, Pulse Width = 10 μs)	t _{on}	—	—	1	μs
Turn-Off Time (I _{TM} = 10 A, I _R = 10 A) (I _{TM} = 10 A, I _R = 10 A, T _J = 100°C)	t _{off}	—	25 40	—	μs
Forward Voltage Application Rate (T _J = 100°C, V _D = Rated V _{DRM})	dv/dt	—	50	—	V/μs

*Indicates JEDEC Registered Data.

